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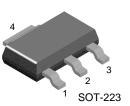


SEMICONDUCTOR

## **NZT753**

## **PNP Current Driver Transistor**

• This device is designed for power amplifier, regulator and switching circuits where speed is important. Sourced from Process 5P.



1. Base 2. Collector 3. Emitter

## Absolute Maximum Ratings\* T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	- 100	V
V <sub>CBO</sub>	Collector-Base Voltage	- 120	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 5.0	V
I <sub>C</sub>	Collector Current - Continuous	- 4.0	А
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ +150	°C

NOTES: 1) These ratings are based on a maximum junction temperature of 150°C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Electrical Characteristics TA=25°C unless otherwise noted

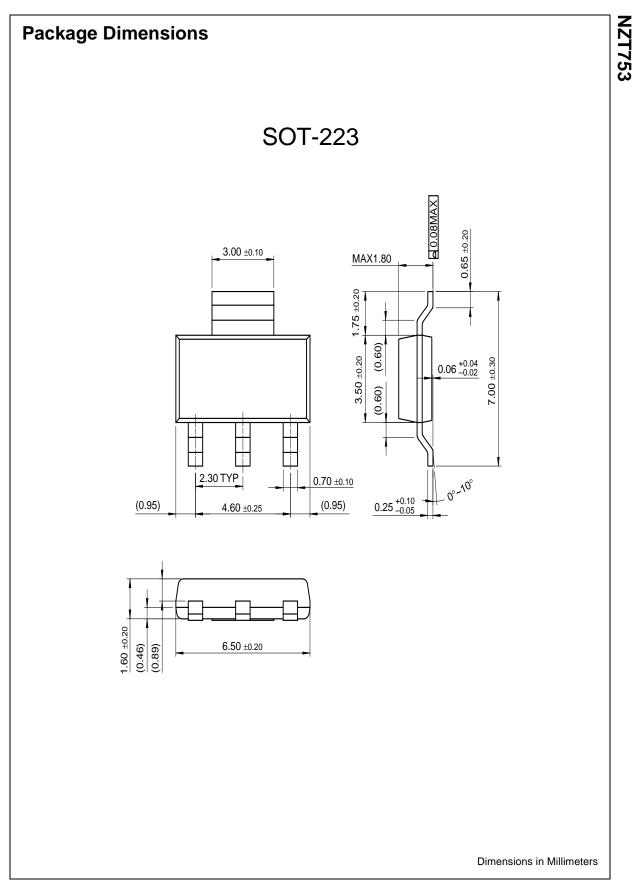
Parameter	Test Conditions	Min.	Max.	Units
teristics	•	•	•	
Collector-Emitter Breakdown Voltage	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$	-100		V
Collector-Base Breakdown Voltage	$I_{\rm C} = -100 \mu {\rm A}, I_{\rm E} = 0$	-120		V
Emitter-Base Breakdown Voltage	$I_{E} = -100\mu A, I_{C} = 0$	-5.0		V
Collector-Base Cutoff Current	$V_{CB} = -100V, I_{E} = 0$		-0.1	μΑ
	$T_A = 100^{\circ}C$		-10	μΑ
Emitter-Base Cutoff Current	$V_{EB} = -4V, I_{C} = 0$		-0.1	μΑ
teristics *				
DC Current Gain	V <sub>CE</sub> = -2.0V, I <sub>C</sub> = -50mA	70		
	$V_{CE} = -2.0V, I_{C} = -500mA$	100	300	
	$V_{CE} = -2.0V, I_{C} = -1.0A$	55		
Collector-Emitter Saturation Voltage	I <sub>C</sub> = -1.0A, I <sub>C</sub> = -50mA		-0.3	V
Base-Emitter Saturation Voltage	I <sub>C</sub> = -1.0A, I <sub>B</sub> = -100mA		-1.25	V
Base-Emitter On Voltage	V <sub>CE</sub> = -2.0V, I <sub>C</sub> = -1.0A,		-1.0	V
al Characteristics	•	•	•	-
Transition Frequency	$V_{CE} = -5V, I_{C} = -100$ mA, f = 100MHz	75		MHz
	teristics Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector-Base Cutoff Current Emitter-Base Cutoff Current teristics * DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage Base-Emitter On Voltage al Characteristics	teristicsCollector-Emitter Breakdown Voltage $I_C = -100\mu$ A, $I_B = 0$ Collector-Base Breakdown Voltage $I_C = -100\mu$ A, $I_E = 0$ Emitter-Base Breakdown Voltage $I_E = -100\mu$ A, $I_C = 0$ Collector-Base Cutoff Current $V_{CB} = -100\nu$ , $I_C = 0$ Collector-Base Cutoff Current $V_{CB} = -100\nu$ , $I_C = 0$ Emitter-Base Cutoff Current $V_{EB} = -4V$ , $I_C = 0$ teristics *DC Current GainDC Current Gain $V_{CE} = -2.0V$ , $I_C = -50mA$ $V_{CE} = -2.0V$ , $I_C = -1.0A$ Collector-Emitter Saturation Voltage $I_C = -1.0A$ , $I_C = -50mA$ Base-Emitter On Voltage $V_{CE} = -2.0V$ , $I_C = -1.0A$ , $I_C = -1.0A$ Base-Emitter On Voltage $V_{CE} = -2.0V$ , $I_C = -1.0A$ , $I_C = -1.0A$	teristicsCollector-Emitter Breakdown Voltage $I_C = -10mA$ , $I_B = 0$ -100Collector-Base Breakdown Voltage $I_C = -100\muA$ , $I_E = 0$ -120Emitter-Base Breakdown Voltage $I_E = -100\muA$ , $I_C = 0$ -5.0Collector-Base Cutoff Current $V_{CB} = -100V$ , $I_E = 0$ -5.0Collector-Base Cutoff Current $V_{CB} = -100V$ , $I_E = 0$ -5.0Emitter-Base Cutoff Current $V_{CB} = -100V$ , $I_C = 0$ -5.0teristics *DC Current Gain $V_{CE} = -2.0V$ , $I_C = -50mA$ 70 $V_{CE} = -2.0V$ , $I_C = -50mA$ 10055Collector-Emitter Saturation Voltage $I_C = -1.0A$ , $I_C = -50mA$ 100Base-Emitter On Voltage $I_C = -1.0A$ , $I_B = -100mA$ alBase-Emitter Saturation Voltage $V_{CE} = -2.0V$ , $I_C = -1.0A$ , $I_B = -100mA$ al	teristicsCollector-Emitter Breakdown Voltage $I_C = -100\mu$ A, $I_B = 0$ -100Collector-Base Breakdown Voltage $I_C = -100\mu$ A, $I_E = 0$ -120Emitter-Base Breakdown Voltage $I_E = -100\mu$ A, $I_C = 0$ -5.0Collector-Base Cutoff Current $V_{CB} = -100\nu$ A, $I_C = 0$ -0.1T_A = 100°C-10-10Emitter-Base Cutoff Current $V_{EB} = -4V$ , $I_C = 0$ -0.1Emitter-Base Cutoff Current $V_{EB} = -4V$ , $I_C = 0$ -0.1Emitter-Base Cutoff Current $V_{CE} = -2.0V$ , $I_C = -50mA$ 70DC Current Gain $V_{CE} = -2.0V$ , $I_C = -50mA$ 100 $V_{CE} = -2.0V$ , $I_C = -1.0A$ 55-0.3Base-Emitter Saturation Voltage $I_C = -1.0A$ , $I_B = -100mA$ -1.25Base-Emitter On Voltage $V_{CE} = -2.0V$ , $I_C = -1.0A$ ,-1.0al Characteristics-1.0

\*Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2.0%

## Thermal Characteristics \* T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
P <sub>D</sub>	Total Device Dissipation	1.2	W
	Derate above 25C	9.7	mW/°C
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	103	°C/W

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